



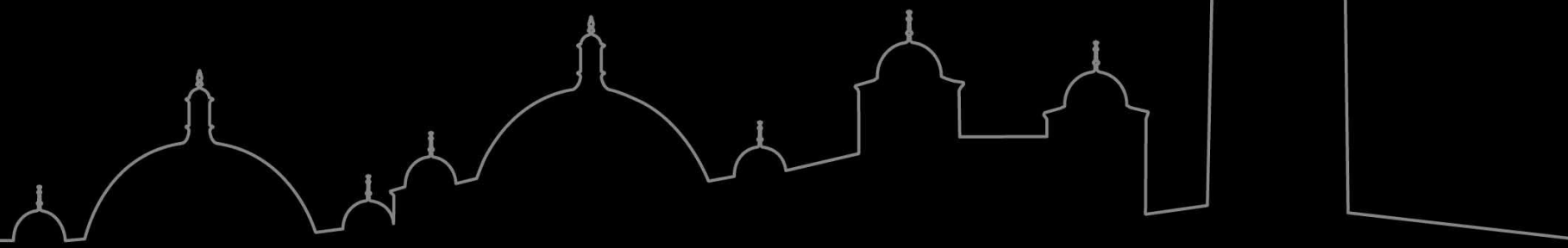
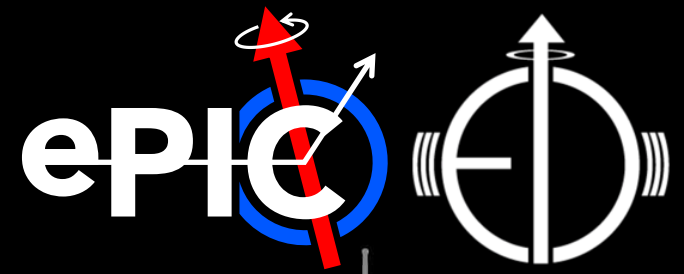
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# ePIC SVT FPC, ancillary ASIC placement, and bonding

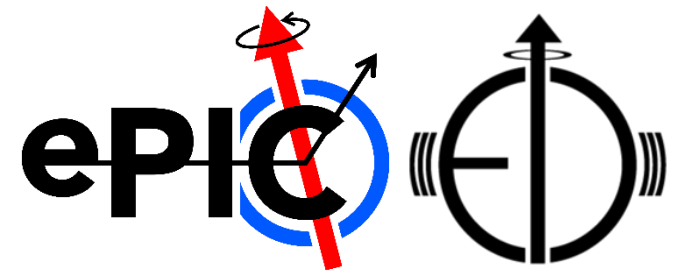
James Glover & Eve Tse

ePIC SVT DSC Meeting

Tue, 26<sup>th</sup> November 2024



# Previous FPC Bonding Discussions

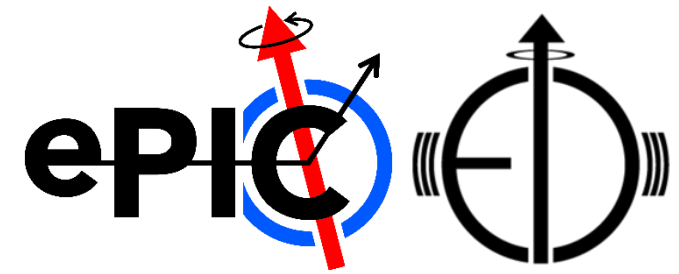


- Bond discussions previously held at WP3 (Electrical Interfaces) and UK meetings:  
<https://indico.bnl.gov/event/23952/#3-prototyping-ob-fpc>
- These have compared the FPC bond options:
  - spTAB – LTU’s recommended bond technique.
  - Wire bonding – likely to be required for EIC-LAS (inherited from MOSAIX).
- Current baseline is to use just **one** bond method between bridge FPC (b-FPC) and chips\*.
  - If LAS **requires** wire bonding, this is preferred for AncASIC also.

\* (EIC-LAS or AncASIC).



# FPC – 2 layer circuit



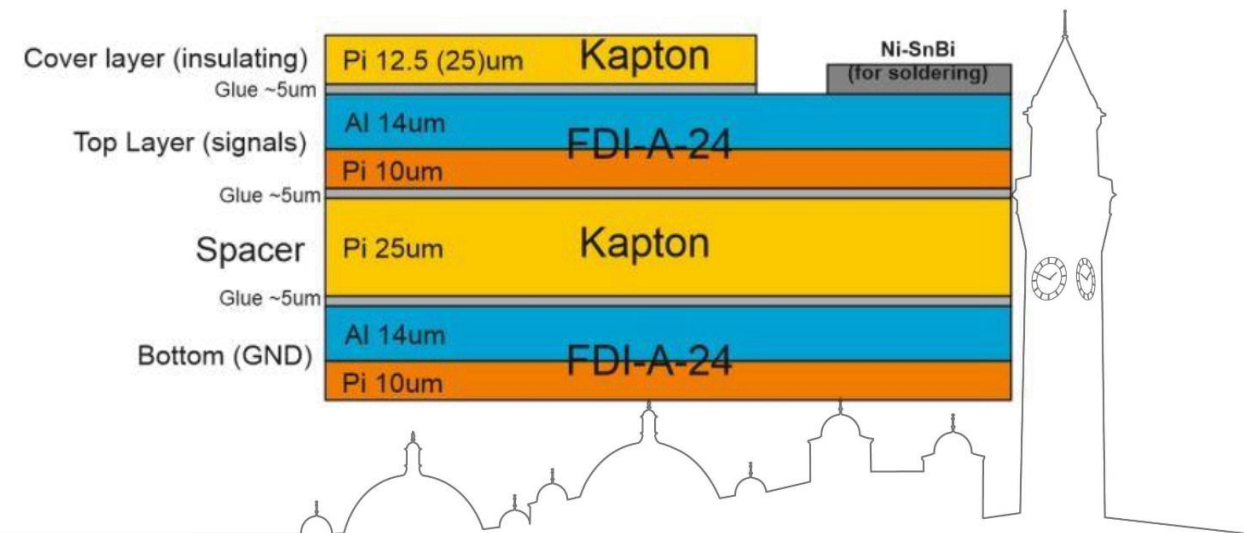
The FPCs (of the OB and discs) are only to have 2 conductor layers.

- No option for overlapping tracks.

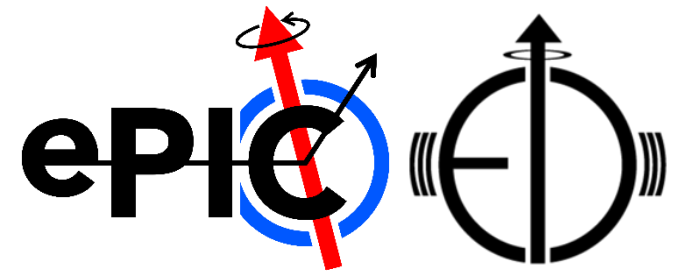
For connections between AncASIC and EIC-LAS:

- FPC can be used as pitch adaptor.
- FPC can't be a redistribution layer.
- $\therefore$  AncASIC pads need to mirror EIC-LAS (MOSAIX) pads.

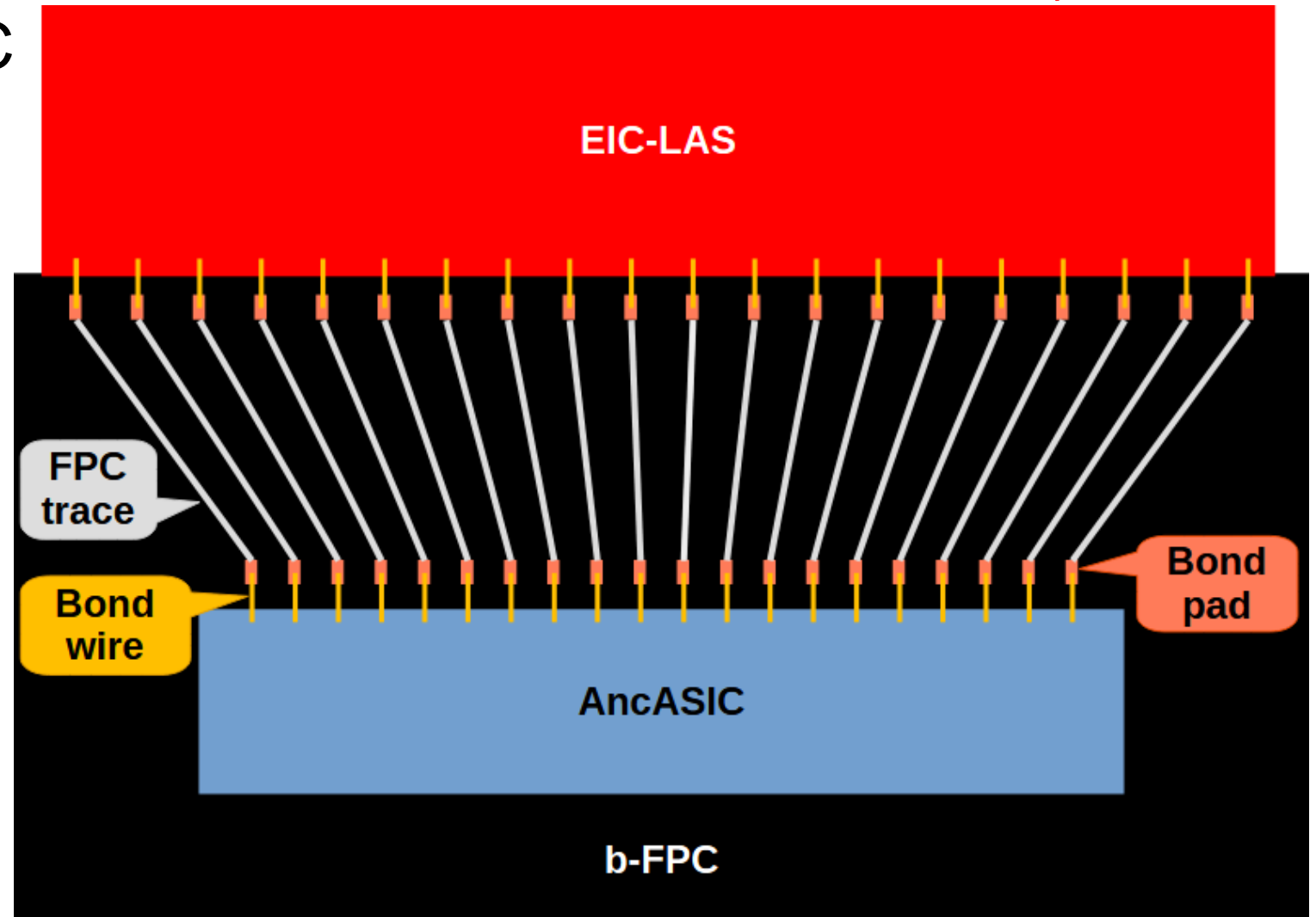
Base cross-section of M-FPC and B-FPCs



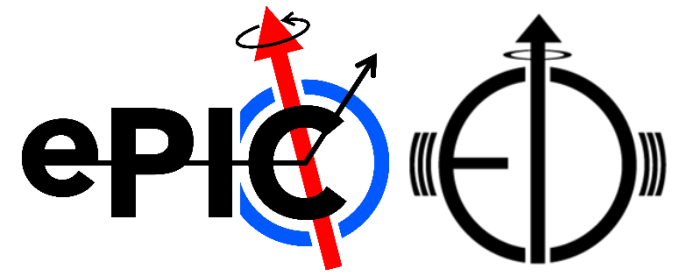
# FPC as a pitch adaptor



- EIC-LAS and AncASIC are different widths.
- # of bond pads are similar.
- $\therefore$  pad pitch must differ.
- FPC traces are used to change pitches.
- Wire bonds stay parallel.



# Number of bond pads on MOSAIX



- Currently this has not been made public.
- This could be because ITS3 are still finalising the MOSAIX design and pads may still change.
- Test PCBs are being designed for the full MOSAIX chip, a near final pad layout should exist.
- Best guess is between 80 and 150 bond pads
- At a pad pitch of  $100\ \mu\text{m}^*$ , this is a pad array length between 8 and 15 mm.
  - This is half the pitch currently on the prototype FPC\*.

\*  $50\ \mu\text{m}$  pad,  $50\ \mu\text{m}$  gap (assumed minimum for  $25\ \mu\text{m}$  bond wire).

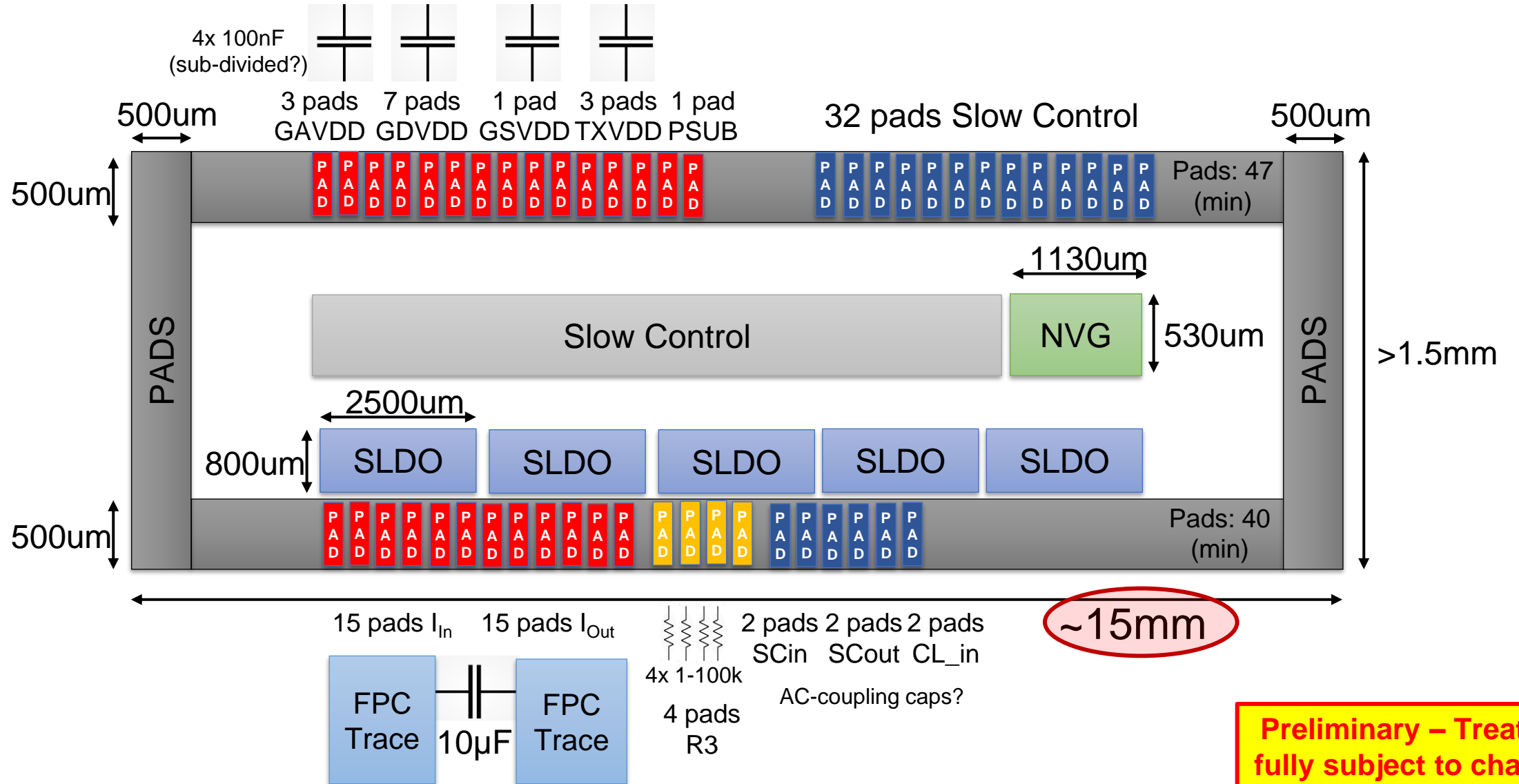
\*  $70\ \mu\text{m}$  trace width,  $130\ \mu\text{m}$  gap.



# AncASIC Size and Pads

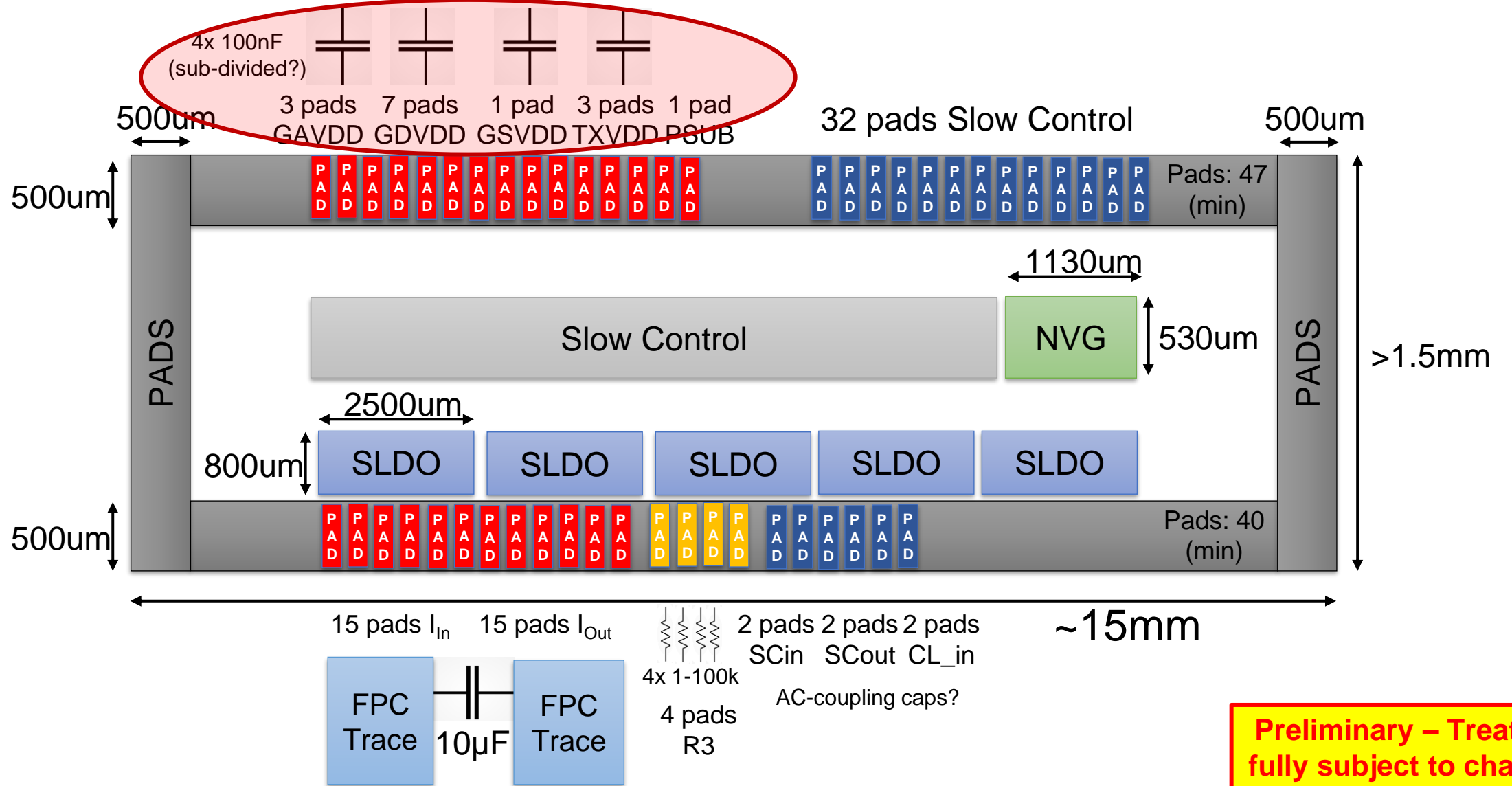
From Iain Sedgwick (STFC):

<https://indico.cern.ch/event/1463541/contributions/6226081>



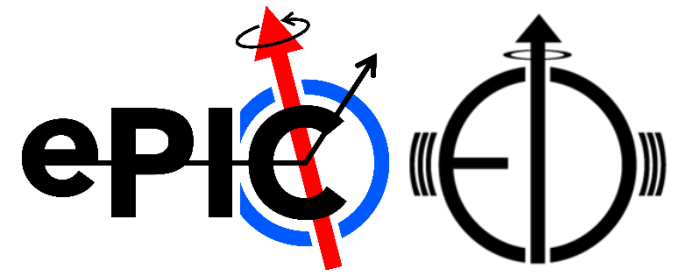
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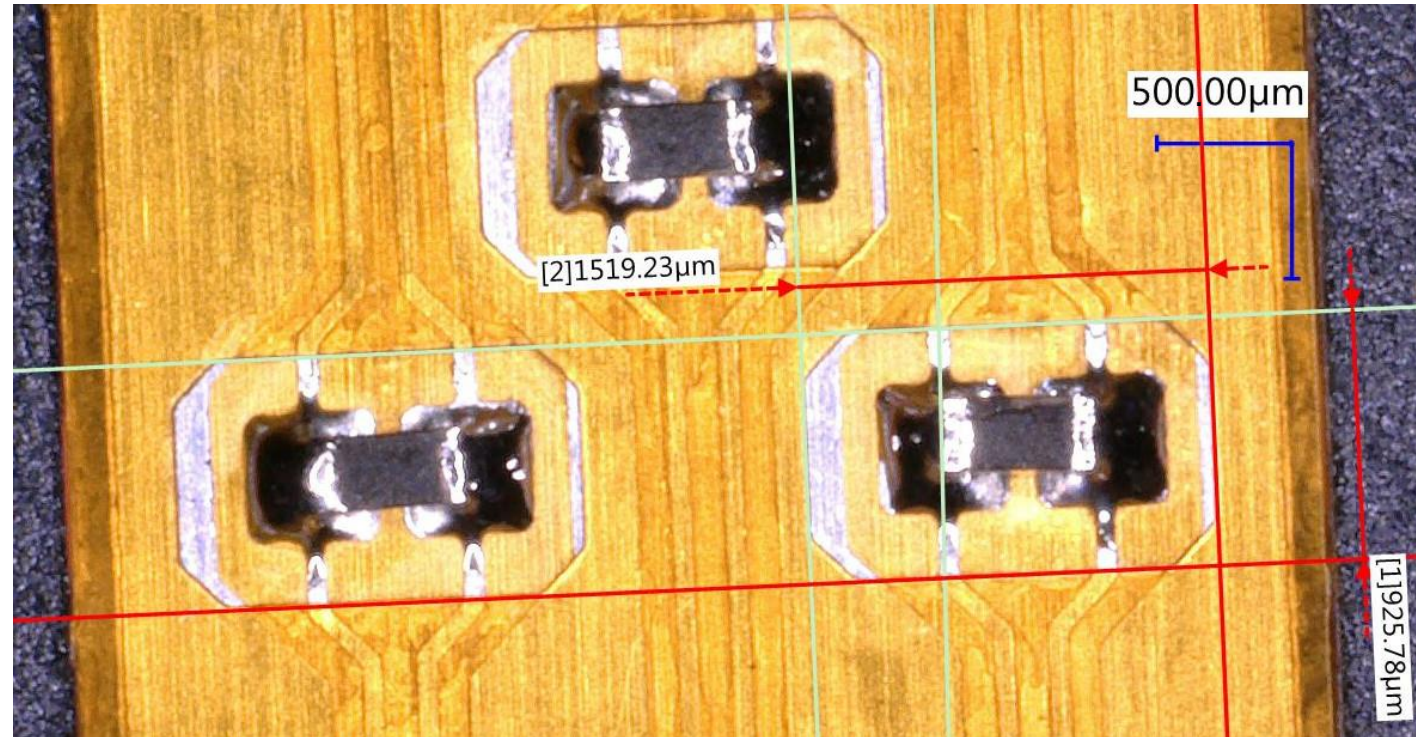
**Preliminary – Treat as fully subject to change**

# Caps between AncASIC & LAS



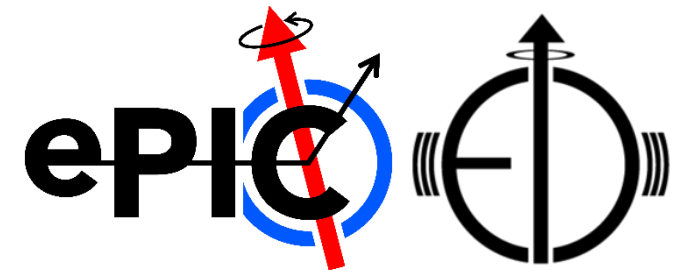
Example from LTU-made prototype FPC.

- On FPC components: 0201 (imperial).
- Sit within a  $1 \times 1.5$  mm window.
- Exact position on b-FPC depends on location of (MOSAIX) pads for the power domains.
  - Number of caps needed is still to be determined.

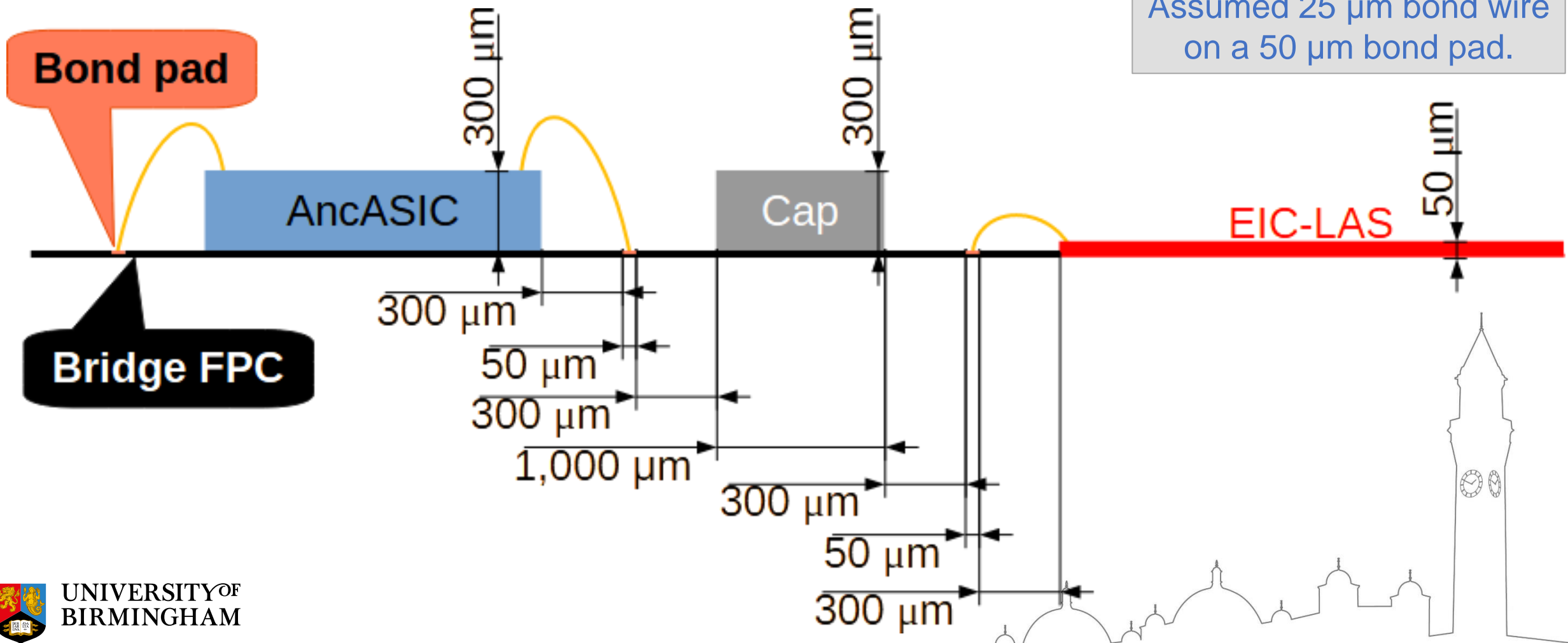




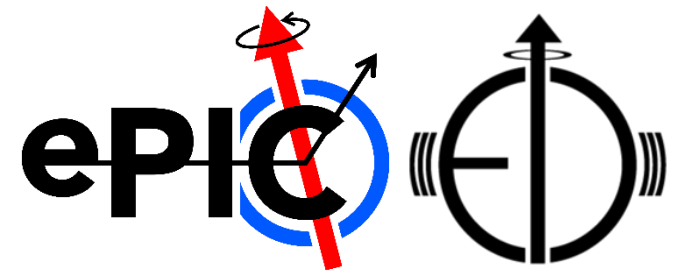
# Wire bond spacing



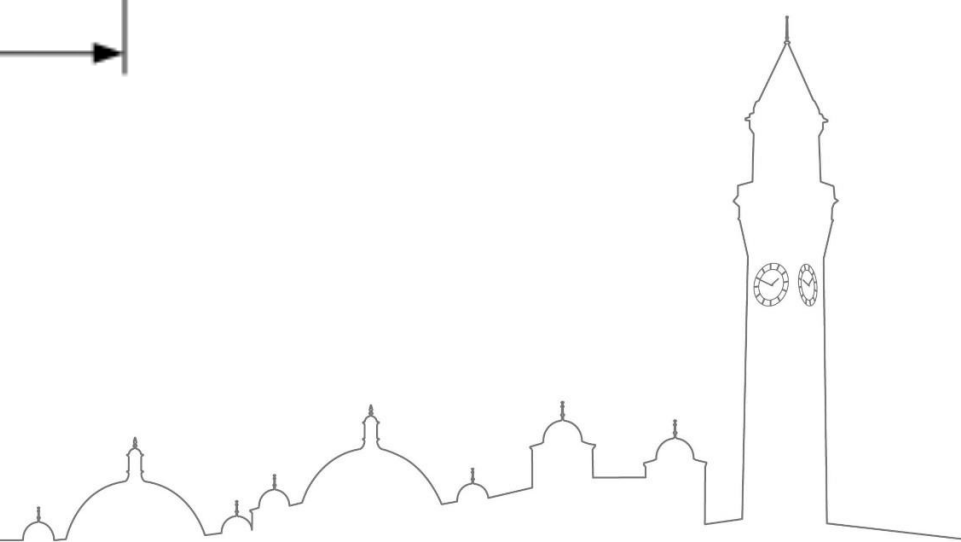
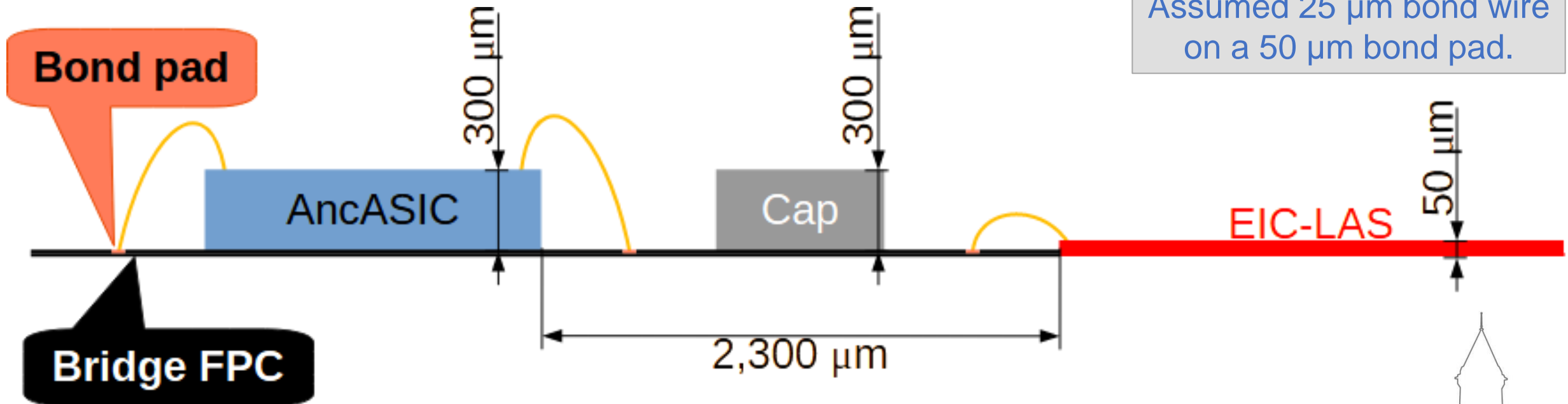
Assumed 25  $\mu\text{m}$  bond wire on a 50  $\mu\text{m}$  bond pad.



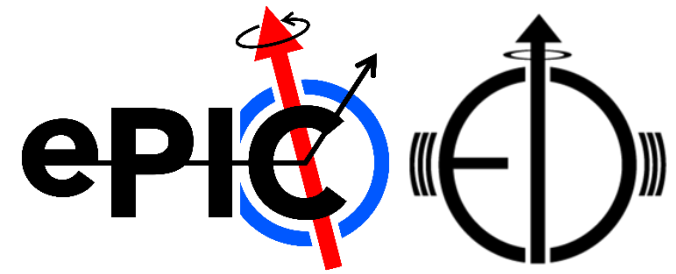
# Wire bond spacing



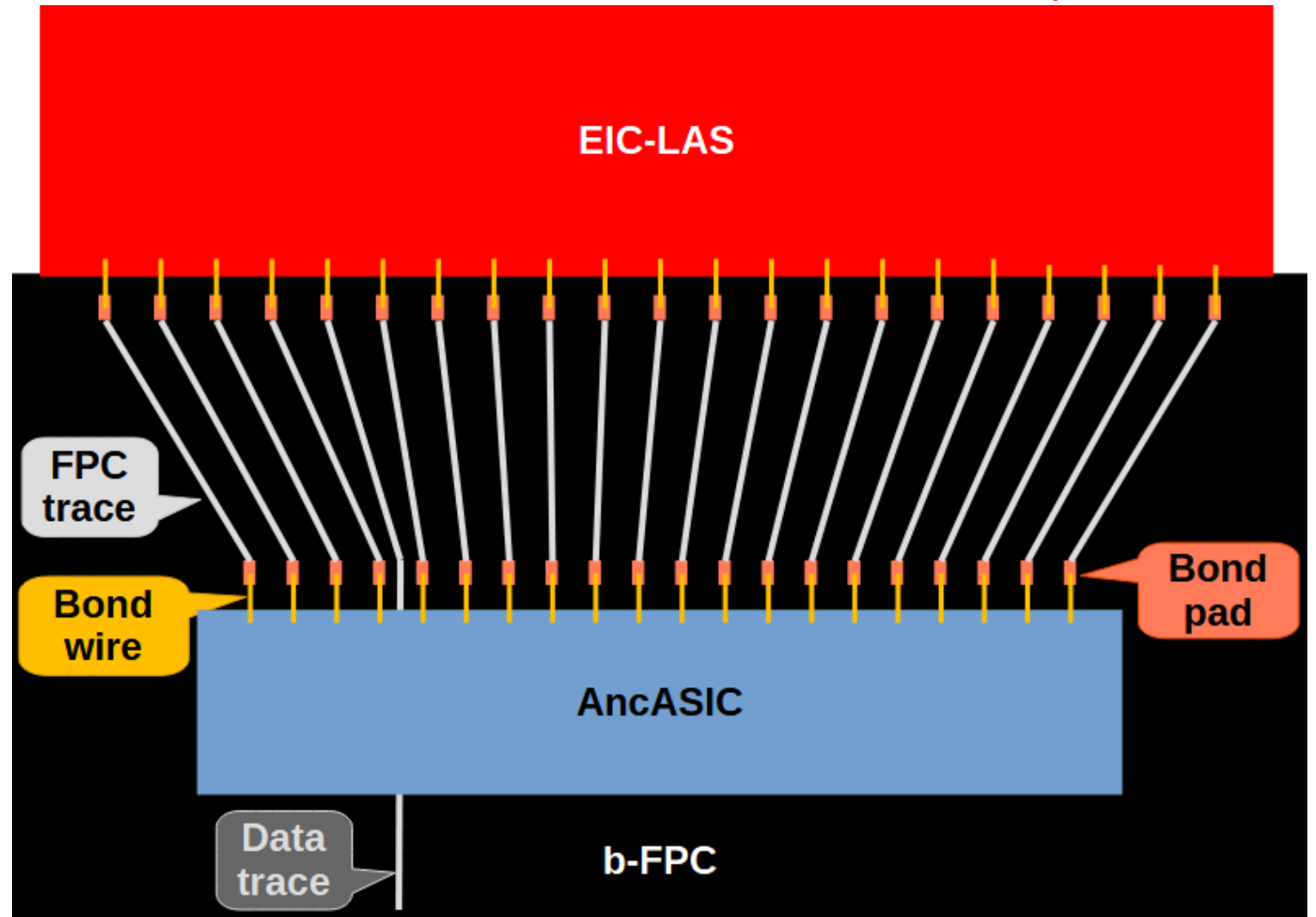
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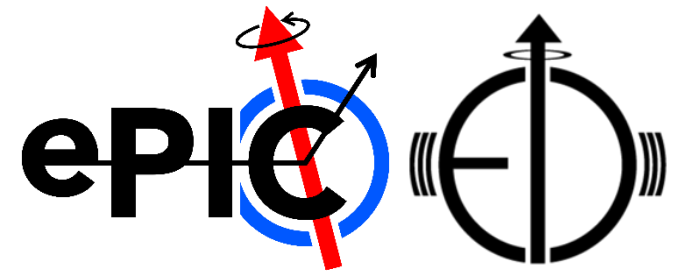
# Data lines are not part of AncASIC



At least one data trace will need to be run under the AncASIC.

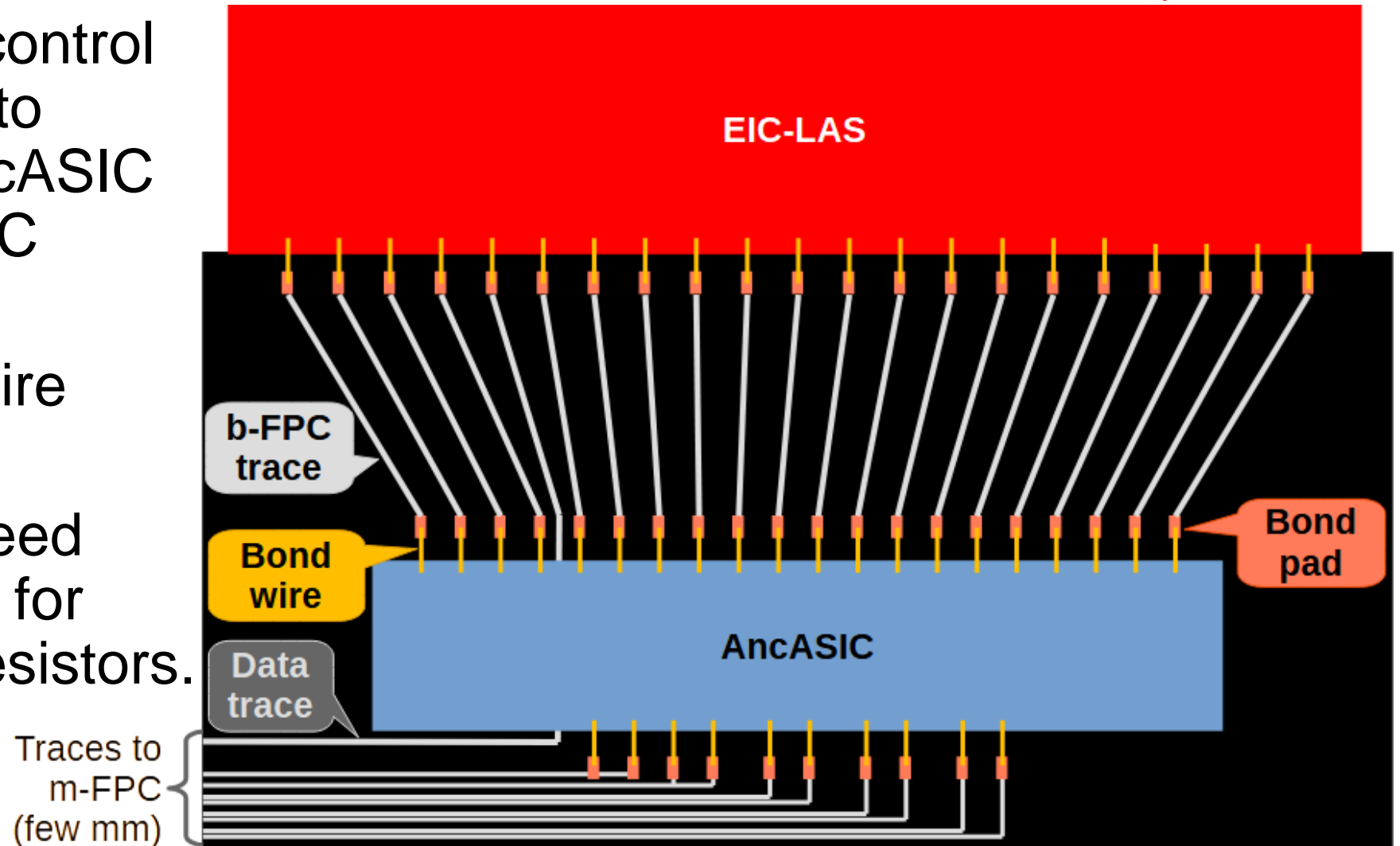


# Traces also come into AncASIC



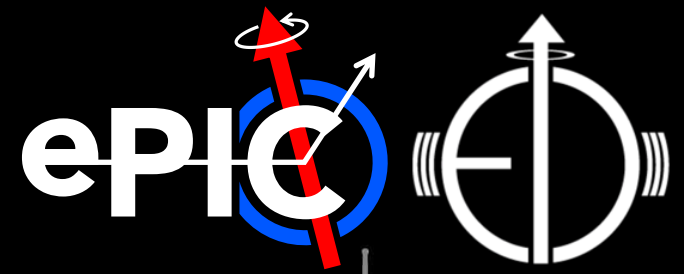
Power and slow control traces also need to come into the AncASIC from the main FPC (m-FPC).

- Power will require many pads!
- S-LDOs also need additional pads for configuration resistors.





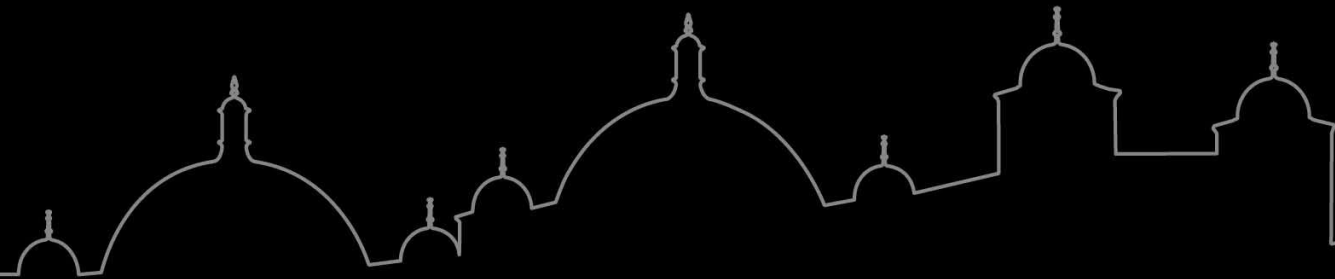
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# Thank you very much!

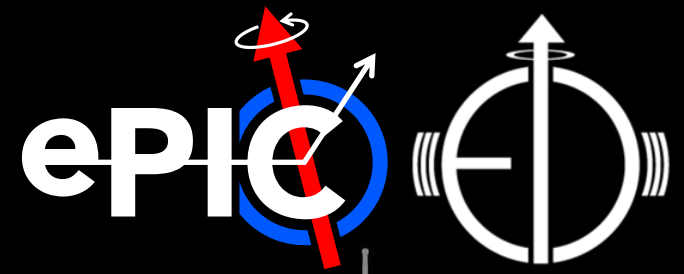
(Especially to I. Tymchuk & others @ LTU, M. Borri, A. Hill, I. Sedgewick, G. Viehhauser)

Any questions?

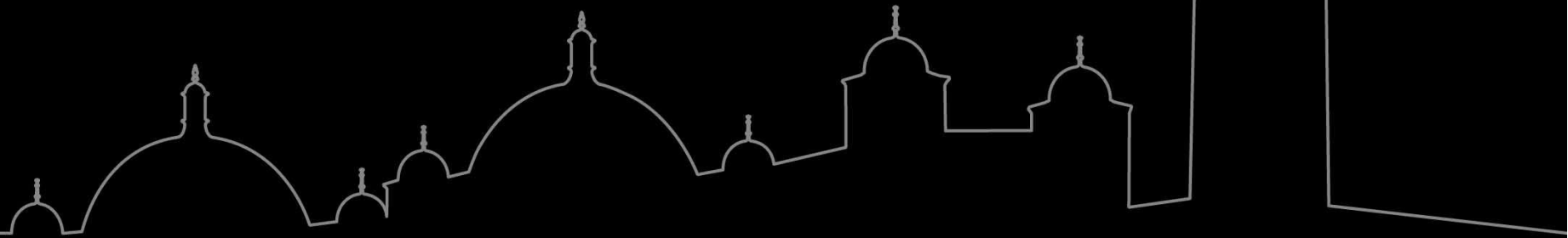




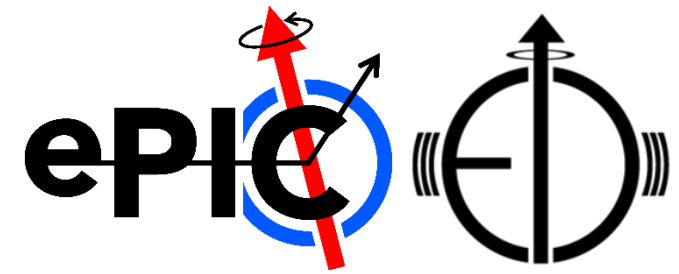
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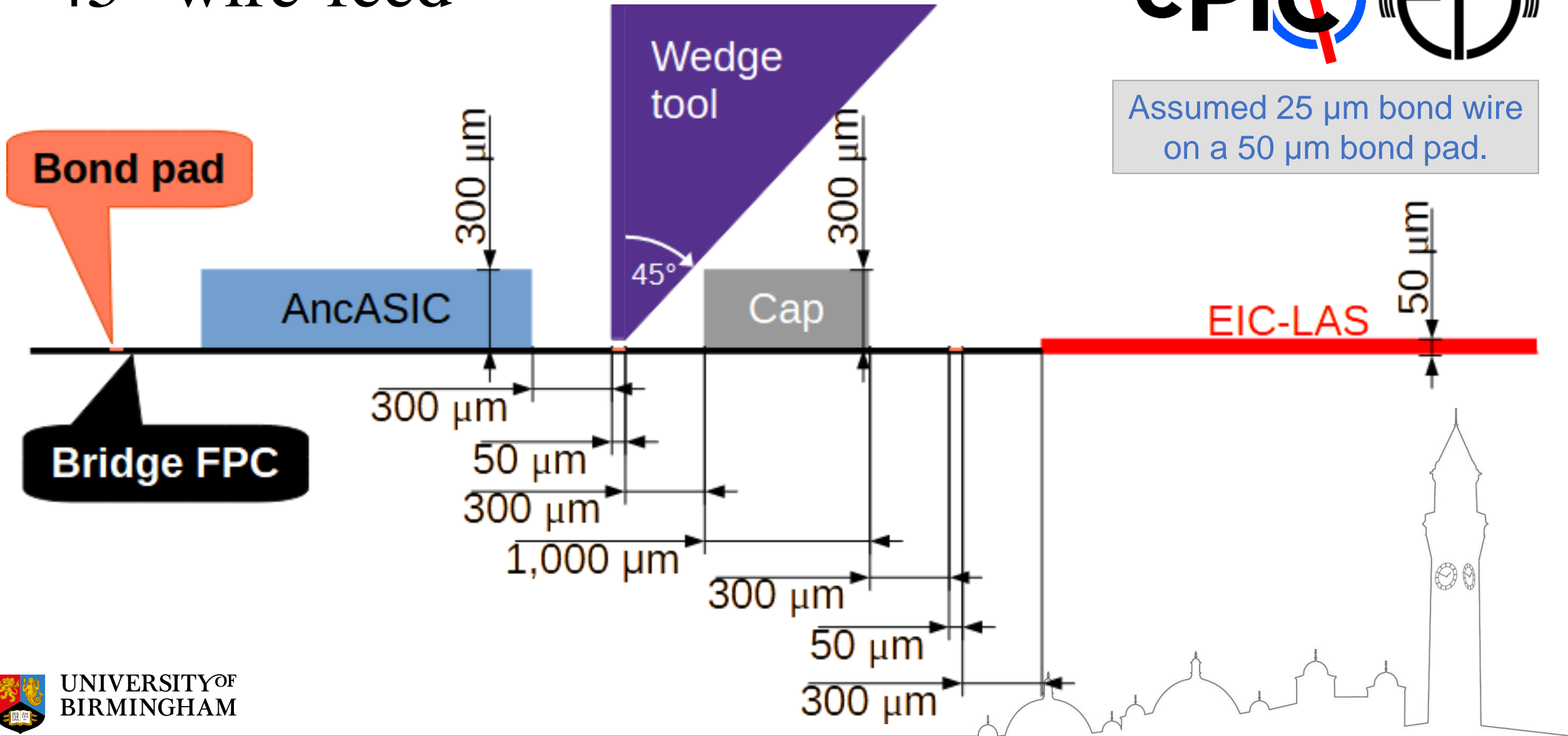
Additional (support) slides



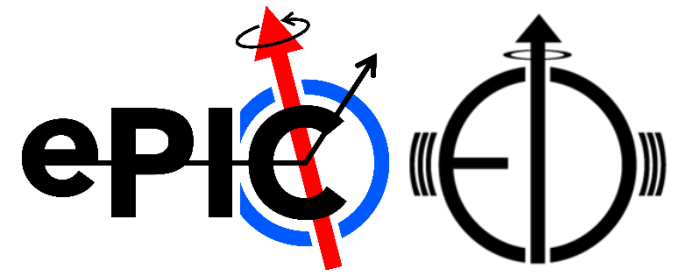
# 45° wire-feed



Assumed 25 μm bond wire on a 50 μm bond pad.



# Connections needed



- The AncASIC is needed for the powering and slow controls.
- Data can be readout from EIC-LAS directly.

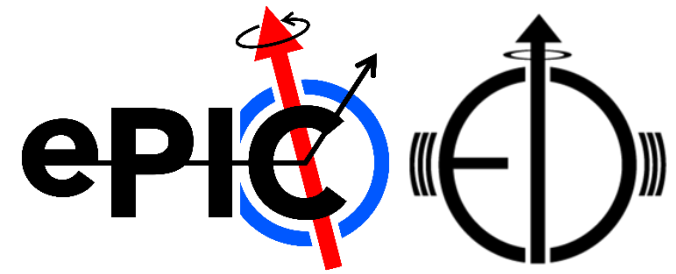
Element	Power	Data	Slow Controls
EIC-LAS	✓	✓	✓
AncASIC	✓	X*	✓
FPC	✓	✓	✓

\* Adding data connections to the AncASIC would just be a passthrough (EIC-LAS to AncASIC to FPC). Why add the extra connection point (point of failure)? However, it is only 1 channel (2 pads/traces).





# spTAB vs wire bonding

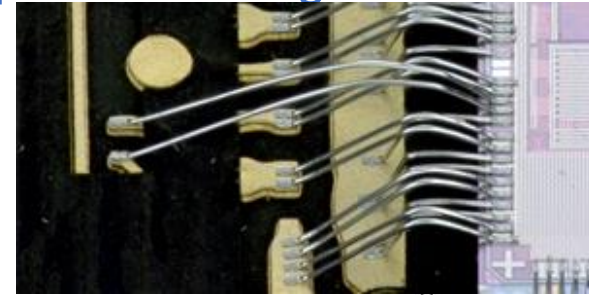
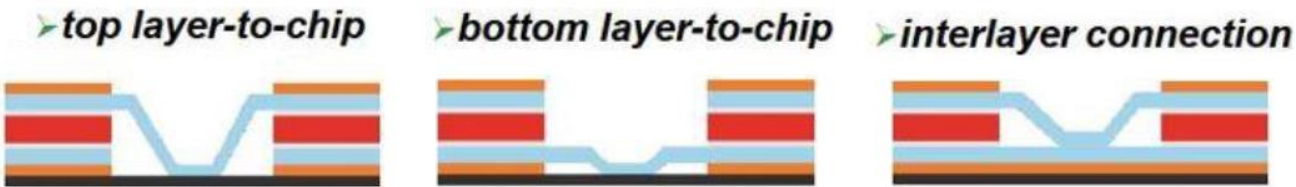


## spTAB

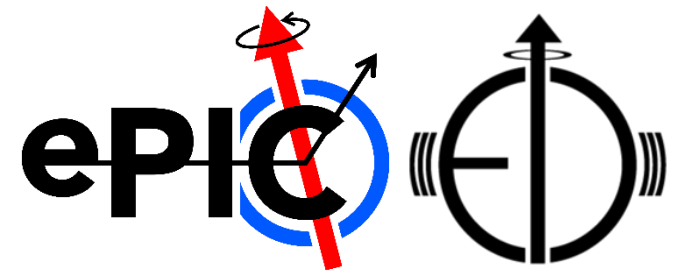
- FPC traces have opening in support at bond locations.
- Aluminium trace (of FPC) is directly welded to a pad on the chip\*.
- Foil width:  $\sim 70 \mu\text{m}$ .
- Best when FPC is **above** the chip\*.
- Recommended by LTU.
  - **Wire bonding to FPC is possible.**

## Wire bonding

- Wire connection between pads on 2 separate substrates (chip\* or FPC).
- Wire width:  $\sim 25 \mu\text{m}$  (15-50  $\mu\text{m}$ )
- Best when FPC is **below** the chip\*.
- The current base-line for the ITS3 MOSAIX chip.
  - **spTAB is being considered.**



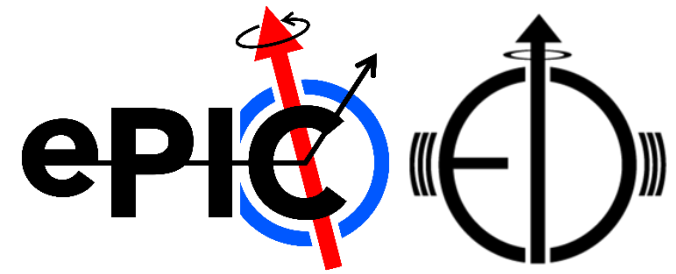
# AncASIC vs EIC-LAS



- We are designing the AncASIC – we can dictate pad size, shape, pitch, and location.
- EIC-LAS (based on MOSAIX) will have a pad design dictated by ITS3.
  - If they finalise a pitch too small for spTAB, we will have to wire bond!
- Mixed bonding is possible (spTAB for AncASIC and wire bonds for EIC-LAS), but the FPC would have to bend from top of AncASIC to bottom of EIC-LAS (assumed **300  $\mu\text{m}$**  height difference).
- The FPC has a min bend radius of 5 mm, this dictates a **2.5 mm (larger) gap between chips to account for the curve!**

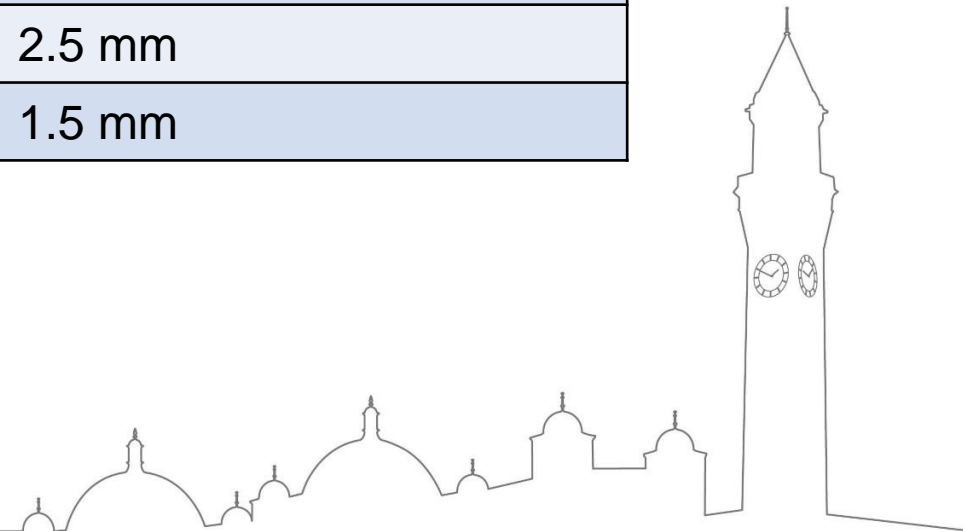


# AncASIC thickness

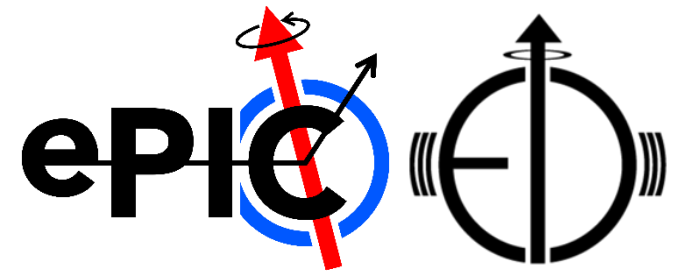


Changing the thickness of the AncASIC would adjust the minimum spacing between AncASIC and EIC-LAS, if mixing spTAB and wire bonding.

AncASIC thickness ( $\mu\text{m}$ )	Spacing needed to accommodate 5mm bend radius of FPC
725 (assumed default)	3.8 mm
300 (easily thinned to)	2.5 mm
100 (added complexity)	1.5 mm

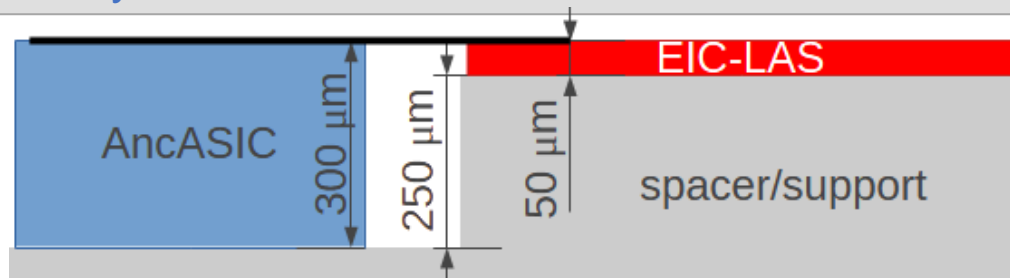


# All spTAB

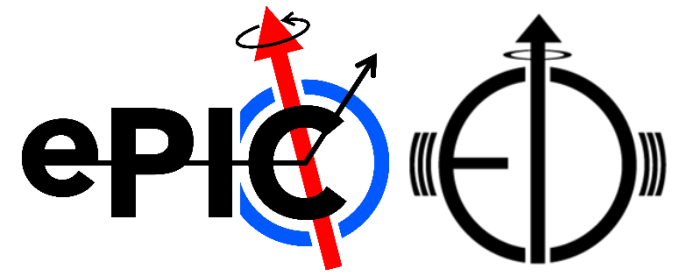


- One bond process would make the production easier.
- To avoid the spacing implication of different surface heights, top of EIC-LAS and AncASIC need to be level.
  - Requires tooling to account for different chip thicknesses.
- Sites (currently) have more expertise with wire bonding.
  - Time needed to change wedge tools in bond machines.
  - Machines (currently) shared with other projects that require wire bonds.
  - A lot of tool changes to accommodate the many projects\*.

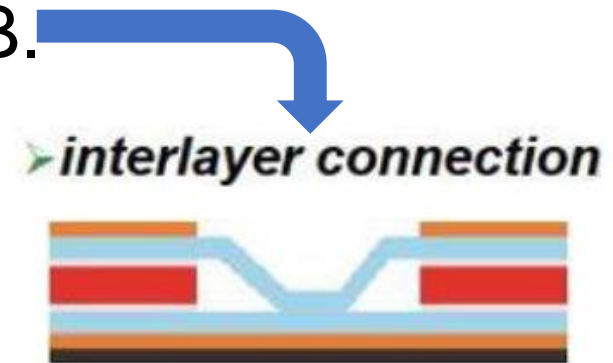
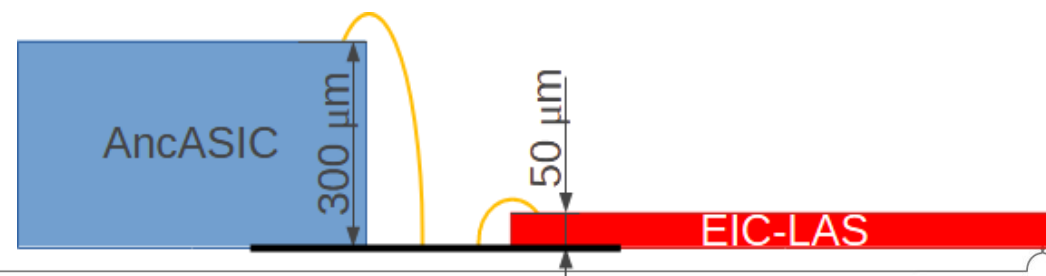
\* May be less of an issue if/when a dedicated bonder is available.



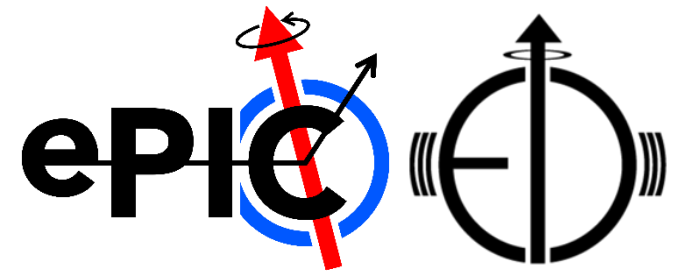
# All wire bonds



- One bond process would make the production easier.
- Sites (currently) have more expertise with wire bonding.
  - No time lost due to changing wedge tools in bond machines.
  - Easier to share machines across projects.
- No special tooling required to get surfaces level.
- FPC interlayer connections still need spTAB.
  - Therefore, we would need to request this to be done by LTU.

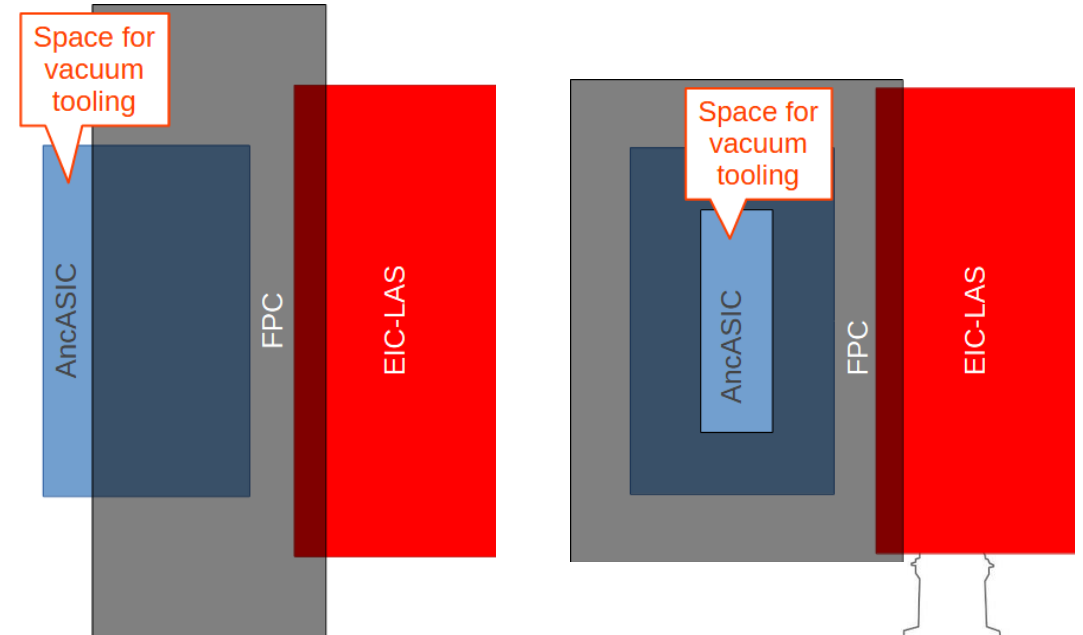


# FPC design to fit assembly

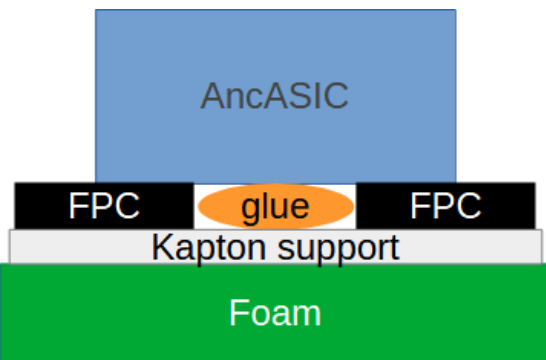


Regardless of whether the FPC is above or below the AncASIC, there are still complications.

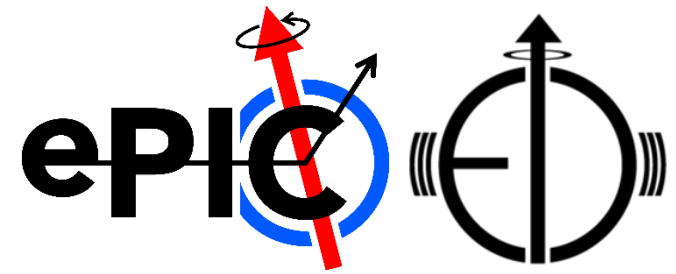
- FPC above (spTAB) – we need space for vacuum tooling to pick up the AncASIC (opening in FPC or uncovered edge).
  - Relying on bonds to hold AncASIC!



- FPC below (wire bond) – we want good thermal path to carbon foam (conductive glue within opening on FPC).
  - Relying on glues to hold FPC and Kapton!



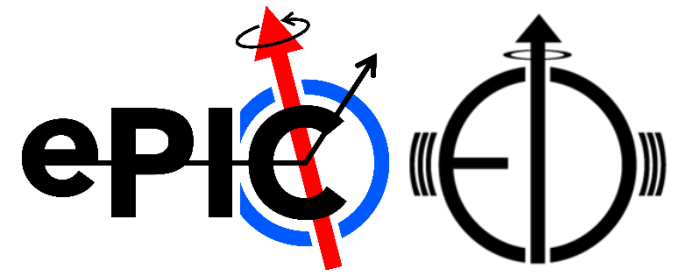
# Mixing flat and curved silicon



- Mixing a flat AncASIC on a curved stave adds complexity.
- To build modules flat, there needs to be enough tolerance in Kapton support layer and FPC to still follow curvature of stave.
- Can not bond a flat surface to a curved surface.
- We become very dependant to finding the right glues.
  - For structural support, while enabling curvature and a thermal path.
- Assembly sequence is dictated by bond choice.
  - spTAB (FPC above chip), or wire bond (FPC below chip).



# Should we bond chip-chip?



- We could bond directly between AncASIC and EIC-LAS (without interconnects through the FPC) – assuming bond angles fit with different chip widths and predominately on 1 chip edge.
- Data channel would need to be bonded directly to FPC (from EIC-LAS).
- Requires the data channel to be located conveniently (e.g. near to one edge of EIC-LAS).

